

STB80NF55-08T4 STP80NF55-08, STW80NF55-08

N-channel 55 V, 0.0065 Ω, 80 A, TO-220, D²PAK, TO-247 STripFET™ Power MOSFET

Features

Туре	V _{DSS}	R _{DS(on)} max	I _D
STB80NF55-08T4	55 V	< 0.008 Ω	80 A
STP80NF55-08	55 V	< 0.008 Ω	80 A
STW80NF55-08	55 V	< 0.008 Ω	80 A

■ Standard threshold drive

Application

Switching applications

Description

This Power MOSFET is the latest development of STMicroelectronics unique "single feature size" strip-based process. The resulting transistor shows extremely high packing density for low onresistance, rugged avalance characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

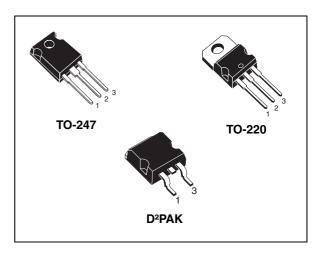


Figure 1. Internal schematic diagram

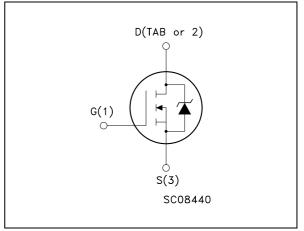


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB80NF55-08T4	B80NF55-08	D ² PAK	Tape and reel
STP80NF55-08	P80NF55-08	TO-220	Tube
STW80NF55-08	W80NF55-08	TO-247	Tube

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1 Electrical ratings

Table 2.	Absolute	maximum	ratings
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Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage ($V_{GS} = 0$)	55	V
V _{GS}	Gate- source voltage	±20	V
I _D ⁽¹⁾	Drain current (continuos) at $T_C = 25 \ ^{\circ}C$	80	А
I _D ⁽¹⁾	Drain current (continuos) at T _C = 100 °C	80	А
I _{DM} ⁽²⁾	Drain current (pulsed)	320	А
P _{TOT}	Total dissipation at $T_C = 25 \ ^{\circ}C$	300	W
	Derating factor	2	W/°C
T _j T _{stg}	Operating junction temperature Storage temperature	-55 to 175	°C

1. Current limited package

2. Pulse width limited by safe operating area

Symbol	Parameter	Value			Unit
Symbol	Falameter	D ² PAK	TO-220	TO-247	Unit
R _{thj-case}	Thermal resistance junction-case max		0.5		°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	35 ⁽¹⁾	62.5	50	°C/W
Τ _Ι	Maximum lead temperature for soldering purpose	300			°C

1. When mounted on 1 inch² FR-4 board, 2 oz Cu

 Table 4.
 Avalanche characteristics

Symbol	Parameter	Max value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _j max)	40	A
E _{AS}	Single pulse avalanche energy (starting $T_j = 25 \text{ °C}, I_D = I_{AR}, V_{DD} = 30 \text{ V}$)	1000	mJ



2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

	On/on states					
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \ \mu A, \ V_{GS} = 0$	55			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = max rating V_{DS} = max rating@125 °C			1 10	μΑ μΑ
I _{GSS}	Gate body leakage current (V _{DS} = 0)	$V_{GS} = \pm 20 V$			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, \ I_D = 250 \ \mu A$	2	3	4	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 40 A		0.0065	0.008	Ω

Table 5. On/off states

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V_{DS} =15 V , I_{D} = 18 A		40		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0		3740 830 265		pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 27 V, I_D = 80 A V_{GS} =10 V (see Figure 14)		112 20 40	155	nC nC nC

1. Pulsed: pulse duration=300 µs, duty cycle 1.5%

Table 7.	Switching	times
	Owncoming	unico

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r t _{d(off)} t _f	Turn-on delay time Rise time Turn-off-delay time Fall time	$V_{DD} = 27 \text{ V}, I_D = 40 \text{ A}$ $R_G = 4.7 \Omega V_{GS} = 10 \text{ V}$ (see Figure 13)		20 110 75 35		ns ns ns ns



Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I _{SD}	Source-drain current				80	А
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				320	А
V_{SD}	Forward on voltage	$I_{SD} = 80 \text{ A}, V_{GS} = 0$			1.5	V
t _{rr} ⁽²⁾ Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80 \text{ A}, V_{DD} = 25 \text{ V}$ di/dt=100 A/ μ s, $T_j = 150 \text{ °C}$ (see Figure 18)		80 230 5.7		ns nC A

 Table 8.
 Source drain diode

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = $300\mu s$, duty cycle 1.5%



2.1 Electrical characteristics (curves)

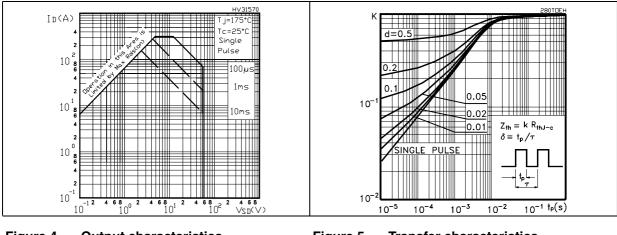
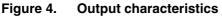


Figure 2. Safe operating area

Figure 3. Thermal impedance





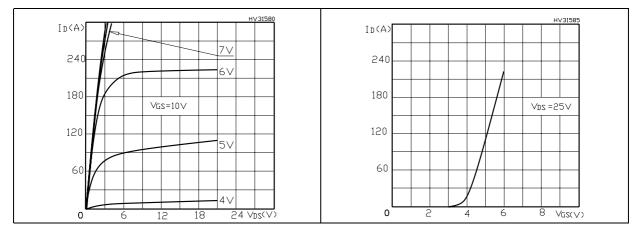
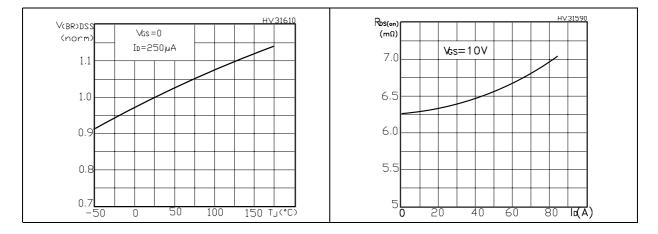


Figure 6. Normalized BV_{DSS} vs temperature Figure 7. Static drain-source on resistance





Gate charge vs gate-source voltage Figure 9. Figure 8. **Capacitance variations**

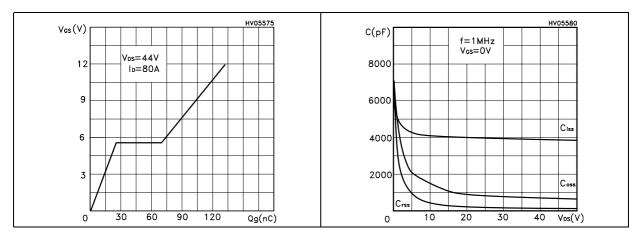


Figure 10. Normalized gate threshold voltage Figure 11. Normalized on resistance vs vs temperature

temperature

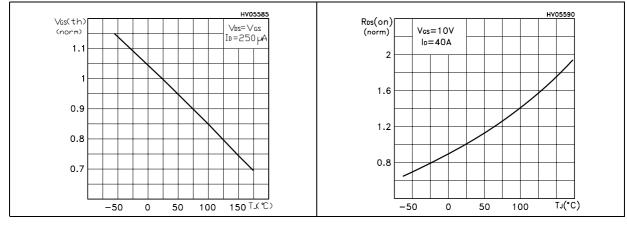


Figure 12. Source-drain diode forward characteristics

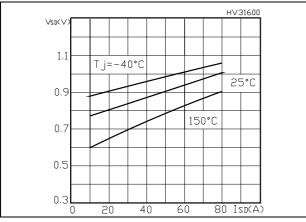


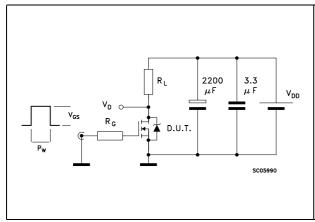


Figure 14. Gate charge test circuit

circuit

3 **Test circuits**

Figure 13. Switching times test circuit for resistive load



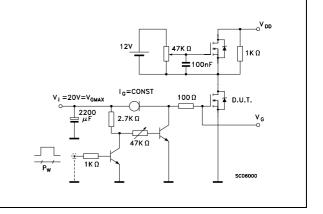
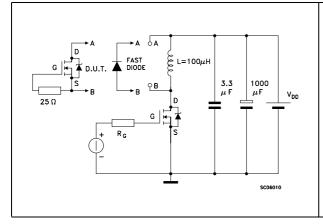
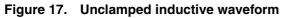
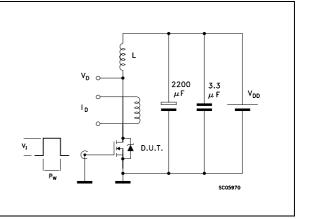


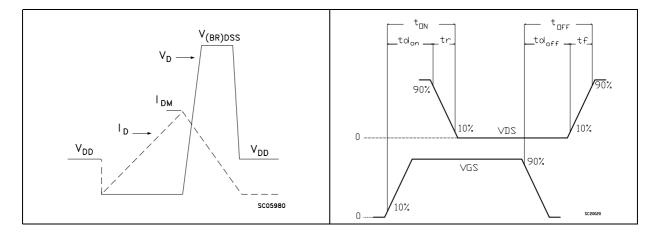
Figure 16. Unclamped inductive load test Figure 15. Test circuit for inductive load switching and diode recovery times











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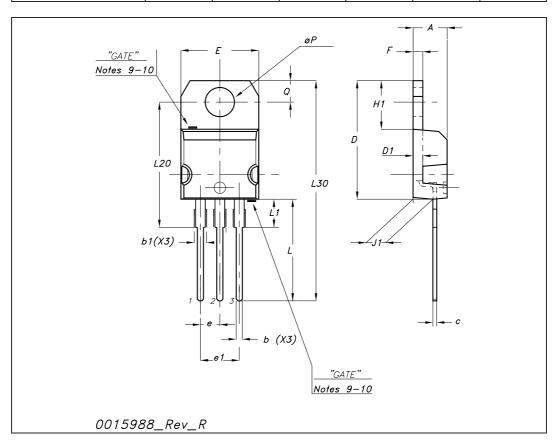
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.



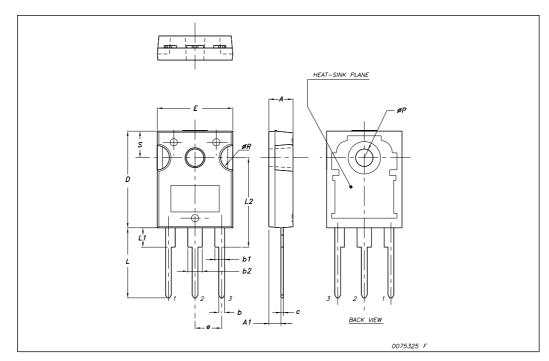
Dim		mm			inch			
Dim	Min	Тур	Мах	Min	Тур	Max		
А	4.40		4.60	0.173		0.181		
b	0.61		0.88	0.024		0.034		
b1	1.14		1.70	0.044		0.066		
С	0.48		0.70	0.019		0.027		
D	15.25		15.75	0.6		0.62		
D1		1.27			0.050			
E	10		10.40	0.393		0.409		
е	2.40		2.70	0.094		0.106		
e1	4.95		5.15	0.194		0.202		
F	1.23		1.32	0.048		0.051		
H1	6.20		6.60	0.244		0.256		
J1	2.40		2.72	0.094		0.107		
L	13		14	0.511		0.551		
L1	3.50		3.93	0.137		0.154		
L20		16.40			0.645			
L30		28.90			1.137			
ØP	3.75	İ	3.85	0.147		0.151		
Q	2.65	İ	2.95	0.104		0.116		







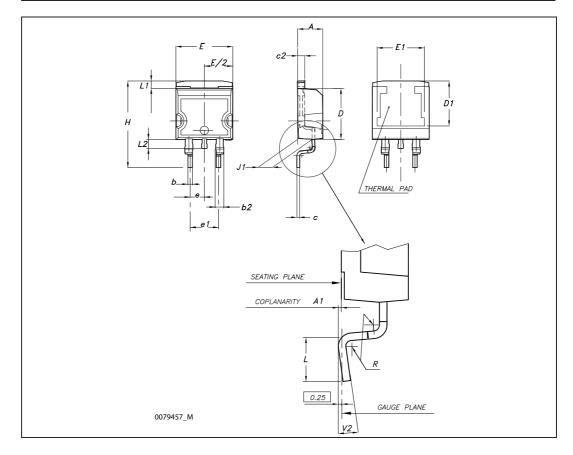
	TO-247 Mechanical data				
Dim.	mm.				
	Min.	Тур	Max.		
Α	4.85		5.15		
A1	2.20		2.60		
b	1.0		1.40		
b1	2.0		2.40		
b2	3.0		3.40		
С	0.40		0.80		
D	19.85		20.15		
E	15.45		15.75		
е		5.45			
L	14.20		14.80		
L1	3.70		4.30		
L2		18.50			
øР	3.55		3.65		
øR	4.50		5.50		
S		5.50			





D ² PAK (TO-263) mechanical data

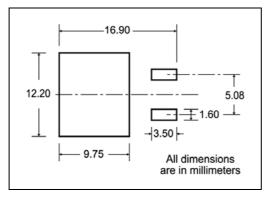
Dim		mm			inch			
	Min	Тур	Max	Min	Тур	Max		
A	4.40		4.60	0.173		0.181		
A1	0.03		0.23	0.001		0.009		
b	0.70		0.93	0.027		0.037		
b2	1.14		1.70	0.045		0.067		
С	0.45		0.60	0.017		0.024		
c2	1.23		1.36	0.048		0.053		
D	8.95		9.35	0.352		0.368		
D1	7.50			0.295				
E	10		10.40	0.394		0.409		
E1	8.50			0.334				
е		2.54			0.1			
e1	4.88		5.28	0.192		0.208		
Н	15		15.85	0.590		0.624		
J1	2.49		2.69	0.099		0.106		
L	2.29		2.79	0.090		0.110		
L1	1.27		1.40	0.05		0.055		
L2	1.30		1.75	0.051		0.069		
R		0.4			0.016			
V2	0°		8°	0°		8°		



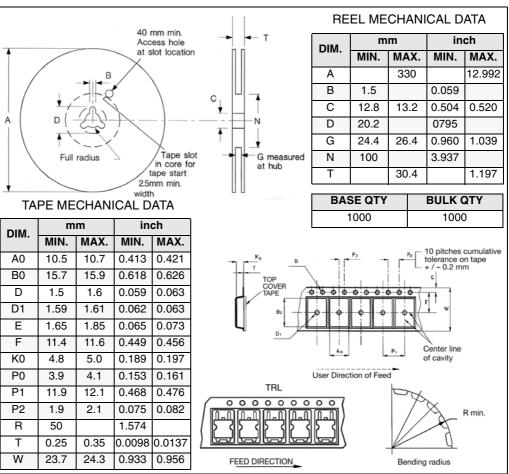


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type



6 Revision history

Table 9.Document revision history

Date	Revision	Changes
03-Mar-2008	1	First release
15-Apr-2009	2	Table 1: Device summary has been updated



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